

FORM PTO-1449		U.S. Department of Commerce Patent and Trademark Office		Atty. Docket No. FIS920030238	Application No. 10/707,842
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)		Applicant Haining S.YANG, et al..			
		Filing Date 01/16/2004		Group 2812	

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EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
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